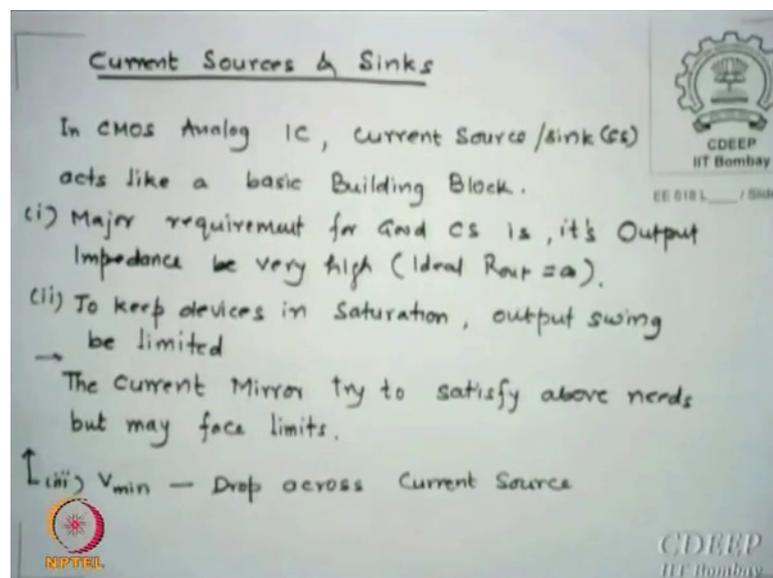


CMOS Analog VLSI Design
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Lecture - 14
Current Sources

And we will tell people come in let us see you what we are looking for, we are at the topic of current sources and sinks.

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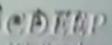
And we have said that in a CMOS analog IC, a current source or sink act like a basic building block. And there are 3 major requirements come from them one of them is that the output impedance should be very high, as high as possible also we must guarantee that the all devices are in saturation and also finally, their mirror should satisfy another limit which is essentially because the both source should have been minimum.

That is dropped across current source should be as small as possible. So, based on these requirements, we already looked into a simple current mirror and we also looked into the variation in parameters a particularly we looked into beta V_T and lambda. Generally lambda parameter variations are very small. So, they need not be taken every time, but for the completeness we did take that and based on that we realize that, if I want to reduce the percentage error between the mirror sources and the output source output current then I must somehow manage variations as small as possible, but there are two

times one positive and negative. So, try to compensate them is that point clear what I said. So, really that word what I am saying the expression which we have derived. There is something that day may be I made mistake, but you can check it yourself again.

(Refer Slide Time: 02:10)

$$\begin{aligned}
 \frac{I_0}{I_{DE1}} &= \left(1 + \frac{\Delta\beta'}{\beta'}\right) \left(1 - \frac{\Delta V_T}{2(V_{GS} - V_T)}\right)^2 \left(1 + \frac{2\Delta V_{DS}}{1 + \lambda V_{DS}}\right) \\
 &= \left(1 + \frac{\Delta\beta'}{\beta'}\right) \left[1 + \frac{2\Delta V_T}{2(V_{GS} - V_T)}\right] \left(1 + \frac{2\Delta\lambda}{\lambda}\right) \\
 &= 1 + \frac{\Delta\beta'}{\beta'} - \left(1 + \frac{\Delta\beta'}{\beta'}\right) \left(\frac{\Delta V_T}{V_{GS} - V_T}\right) \\
 &= 1 + \frac{\Delta\beta'}{\beta'} - \frac{2\Delta V_T}{(V_{GS} - V_T)} - \frac{\Delta\beta'}{\beta'} \frac{2\Delta V_T}{V_{GS} - V_T} \\
 &= 1 + \frac{\Delta\beta'}{\beta'} - \frac{2\Delta V_T}{V_T} \cdot \frac{1}{\left(\frac{V_{GS}}{V_T} - 1\right)} - \frac{\Delta\beta'}{\beta'} \frac{2\Delta V_T}{V_T} \cdot \frac{1}{\left(\frac{V_{GS}}{V_T} - 1\right)} \\
 \text{Typically } \frac{I_0}{I_{DE1}} &= 1 \pm 0.04 \text{ i.e. } \approx 4\% \text{ error}
 \end{aligned}$$

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 We take $1 + \frac{2\Delta\lambda}{\lambda} \approx 1$
 NIPTRIL  CDEEP IIT Bombay

I have a feeling that I think instead of two below the denominator in my expression it is in 2 in numerator. So, this 2 should have something like that some error is do not look this expression look of course, there is a power to the power 4, leaving all higher order terms this is what typically you will get. And I said you that these are the two terms which are essentially governed by delta V T by V T, and there is a term which is delta b dash by b dash. So, if I want to make this as small as possible these two terms must be very close to this term is that clear. So, if that happens only you will tell you can adjust your lengths, widths you can also adjust V G S you can adjust V T possible and then you can minimize the effect of variations.

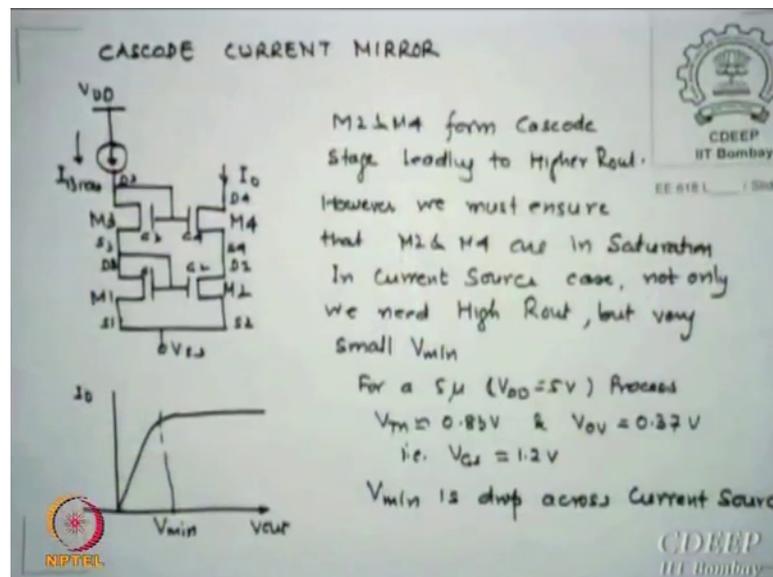
So, there is in case you need a very strong source with no variations one possibility that we can play with the parameters. So, that that can be minimized, of course 4 percent error is normally acceptable in most cases, but in case it is lower than that you require then you must somehow try to see whether we can minimize that delta.

Student: f

F is a function any of them V_T or $\alpha\beta$ or λ whatever it is if any of the variation is 5 percent, then we find typically this is 4 percent error appears is that ok. You can see this is getting subtracted. So, it will be less than major error which is coming ok.

Ok so, this is what we did last time. So, today we start with as I say one of the features of good current source for mirror it show high impedance and it should have (Refer Time:03:58)ok. These are the two major features I want to attend and for this, I will start looking into alternative to simple mirrors and here is the first alternative.

(Refer Slide Time: 04:11)



You already know very well that if you use a CASCODE what do you improve the output resistance. So, the one of the feature of a current source was you need a output resistance higher. So, use a CASCODE part there, so automatically all may actually go high or out should go high, we are also looking for minimization of this. So, we will see that how much we V_{min} get, V_{min} means at the output what is V_{min} you are actually going to get somewhere here. And we will figure it out how much is the actually a minimum dropped across the source which is allowed. So, for example, I have said a typical for a 5 micron process which is given in by a bakers book say V_{Tn} of .83 volt over voltage of .37 volt.

That gives V_{GS} of 1.2 volt please remember where is V_{GS} minus V_T if V_T is .83 and if this is .37 V_{GS} has to be 1.2 volt. Now we want to figure out what is the minimum drop across the current source for this data some numbers since we are going

to calculate I thought I should put the numbers this is taken from (Refer Time:05:25) book data. So, please check the numbers if there is something mistake if I have made hopefully not. So, I am trying to now use a CASCODE mirror, in which I have two stages you can see from here M 3 M 4 forms a pseudo mirrors and M 1 M 2 also form a mirror kind of structure and one is sitting over the other, but if you look at M 2 and M 4 and if this potential for AC is 0 this act like a CASCODE to that.

So, this get connected to the driver is that clear. So, we was trying to see that because of M 4 sitting over M 2 at this point the output resistance should be g_1 times (Refer Time:06:14) plus into I_o . So, that little more, but that is the typical value. So, if I can get that value then I have improved my current source requirement R_{out} should higher that possibility exists. Now we can see from here the way it is done this is a current source which you will actually put it through some P channel device later which is called the bias current which is our reference current. So, you see this button D 3 and S 3, V_{DS3} you know since I am connecting something like this the gate of this V G S and this V G S is same, since I am connecting something like this V G S and this V G S are also same.

Is that ok, however please remember some fun part in that, this V G S has something to do with drop from here, but source is not now at ground potential but this source is at drop V_{DS} across this. So, V G S may be same, but this source is not a ground this has to be understood. So, the gate voltage is not exactly at the ground for the upper ones sorry this potential and it is plus something is adding up, but net value of V G S has to be same if the currents are to be same. So, this idea that what will these two to and what will these two do can be figured out from example given to you. This is still a good current source there is nothing much you can do analysis, but what was interesting to me is this g_s are only return to prove a very which is gate for 1 and drain for 1.

For example, the source of M 3 is drain of M 1, source of M 4 is drain of M 2 and we are interested in this voltage at the end, why we are interested in D 4 because that is the real minimum. So, we want to know what is that minimum in most cases the source. So, what is grounded and not connected to source they are generally grounded, but there are technologies in which it is connected as well. So, different than V S B effects could be taken care in case this is not connected directly, but through a ground if it is a ground that means, there is a potential to there some V T will move.

So, that part will be there right now I am I am not considering V S B effect, but that they can always be brought into the expressions, may be I will give an example when I have brought that expression is that ok. So, let us see the first thing I am worried about what is the V minimum part because R out I by intuition I know because I have put a CASCODE. I am going to get it higher, but I want to know what is the of course, I will calculate that as well, but first let us see what is the V minimum.

(Refer Slide Time: 09:08)

The slide contains a circuit diagram and handwritten calculations. The circuit shows a cascode current source with two NMOS transistors, M1 and M2, connected in series. The gate of M1 is biased at V_{GS} , and the gate of M2 is biased at $V_{GS} + V_{GS}$. The source of M2 is connected to the drain of M1. The output current is I_D . The drain of M1 is at V_{D1} and the drain of M2 is at V_{D2} . The source of M1 is connected to a current source I_{REF} .

Handwritten calculations on the slide:

If $V_{GS} = 1.2\text{ V}$
 then $V_{GS1} = V_{GS2} = 1.2$
 and $V_{GS3} = V_{GS4} = 1.2 + 1.2 = 2.4\text{ V}$

For M4 in Saturation
 $V_{DS4} > V_{GS4} - V_T$ Now $V_{D2} = V_{S4}$

For M2 to saturate $V_{DS2} \geq V_{GS2} - V_T$
 If we keep $V_{DS2} = V_{GS2}$, then M2 is always in Saturation
 $\therefore V_{DS2} = V_{GS1} = V_{GS2} = 1.2\text{ V}$

For M4 to be in Saturation $V_{D1} - V_{D2} \geq V_{GS4} - V_{D2} - V_T$
 or $V_{D1} \geq 2.4 - 0.83 = 1.57\text{ V} = (2V_{OV} + V_T)$
 i.e. $V_{min} \geq 2V_{OV} + V_T$

Logos for COEEP UT Bombay and NPTEL are visible in the corners of the slide.

Let us say for the values given by those bias book V G S is 1.2, let say there are two batteries one is biasing this and one is biasing this, we could say there that V G G 1 which is same as V G G 2 this is coming from the mirror side, please remember this value is coming from the actual reference side. So, it is equivalently saying there is a biased to M 2. Please remember V G S 2 is same as V G S 1. So, I am just writing directly there. So, V G G 1 is V G G 2 which is 1.2 volt, because V G S has been given to me 1.2 volt. Similarly V G S, V G G 3 is equal to V G G 4 from the other side I please remember all that I am doing this and this and this ok.

So, this is equivalently saying the supply coming here. So, which is 1.2 here plus 1.2 here for that V G S so it is 2.4 there. So, for M 4 to be in saturation what is the condition M 4 will be always in saturation, the V D S 4 of M 4 should be larger than V G S minus V T for M 4 is that correct that is the condition which it should satisfy if M 4 to remain in saturation. Now we also now V D 2 which is equal to the V S 4 that is the source of M 4

is same as V_{D2} , let M_2 is saturate the $V_{D S 2}$ or $V_{D 2}$ of this should be larger than $V_{G S}$ minus V_T of this two transistors should remain saturation. So, that the output resistance will act like a CASCODE structure and you will have mirror transitions in a anyway otherwise because this should be same as the other side current.

So, these are the two conditions and if we keep $V_{D S 2}$ is and there is a condition we want to force, what is the minimum $V_{D S 2}$ I should have. If this $V_{D S 2}$ same as $V_{G S 2}$. So, $V_{G S 2}$ minus V_T will be always smaller than $V_{D S 2}$. So, transistor will always remain in saturation if this voltage is same as this voltage as the minimum value of $V_{D 2}$ which allow transistor to saturate, if this equal to this, is they are equal then transition M_2 will always remain in saturation is that correct $V_{G S}$ minus V_T will be always smaller than $V_{D S}$. This value is going to vary with the difference of currents which I will pass through that this is a function of someone yesterday I was asking I am proving it yeah that may vary, but at the up to up to which I will allow it to vary the max minimum value which I should allow is $V_{G S}$ minus V_T should be smaller than $V_{D S}$ will only occur when $V_{G S}$ is same as V_T is that correct.

So, if that mean I am calculating what is the minimum I am not saying at a $V_{O V}$, I am calculating what is the minimum possible available to me. So, M_2 remains saturation with $V_{D S 2}$ equal to $V_{G S 2}$. So, $V_{D S 2}$, $V_{G G 1}$ equal to $V_{G 2}$ is 1.2. So, if I keep it 1.2 volt I am guaranteeing M_2 will always remain in saturation. I am actually interested to know what is this value just a minute because I want to see that upper value also should saturate the upper one. So, I am trying to see both together how much I will saturate is that ok. For M_4 to be saturation $V_{D 4}$ minus $V_{G 2}$ should be greater than $V_{G G 4}$ minus $V_{D 2}$ minus V_T , that is $V_{G S}$ which is V_{D} , $V_{G G 4}$ minus $V_{D 2}$ is $V_{G S}$ minus V_T and this is $V_{D 4}$ minus $V_{D 2}$ is $V_{D S}$ for this condition gives me it should be 2.4 minus .83 substitute the values.

So, around .57 so it is $2 V_{O V}$ plus V_T , now this value has now come that unless I have a $V_{O V}$ which is equal to $2 V_{O V}$, V_T I cannot ensure you now both transition individually $V_{O V}$ sufficient, but together in series I must attend this value. So, that the output of for which I am now calculating both transistor remain in saturation. So, that the minimum now I am now getting is $2 V_{O V}$ plus V_T where it will definitely yeah otherwise you should have to further increase if you want hundred percent guarantee on it, but what is the since $V_{O V}$ is .37 as you said. So, .37 into .74 plus .83. So, it is

roughly 1.57 volt which is required at the output is that correct as the minimum V_{min} so that means, not really doing fantastic job because.

Till 1.57 volt this is not acting like a good current source that is the limit of this, but what is the advantage I got it this I have achieved it I had cleared out that, what is the value I would prefer it should be independent of V_{OV} in such why should I feel it should be independent of V_{OV} because if it is only V_T dependent then I am controlling it. So, I will like to have a current source which is only strongly dependent on V_{DM} nothing else no W bias the; if I get that value I am happy. So, I am trying to reach towards that, but if I use CASCODE, I have a larger V_{D4} requirements I am coming to keep M_2 M_4 in saturation. Now this is an issue which has to be taken because what is a good current source, in some cases may be then you have a sufficient voltage margins.

So, you can still go ahead and work with it, but in other cases this may not be achieved you will actually prefer point some .8 or .7 volt as V_{min} for you, now this calculations are all this to do how much minimum really I can achieve for you, ok is that now I can do without going into detail but as we already done it.

(Refer Slide Time: 15:20)

Rout evaluation

The diagram shows a cascode circuit with a test current source I_x and voltage V_x applied to the output node. The equivalent circuit for R_{out} evaluation is shown with dependent current sources $g_{m4}V_{gs4}$ and $g_{m2}V_{gs2}$, and output resistances r_{o4} and r_{o2} .

$$R_{out} = r_{o4} (1 + g_{m4} r_{o2}) + r_{o2}$$

$$\approx r_{o4} (1 + g_{m4} r_{o2})$$

$$\approx g_{m4} r_{o2} r_{o4} \text{ (Cascode Effect)}$$

To reduce V_{min} , we use additional Battery of V_T between Gates of M_3 & M_4 .

This gives $V_{GS4} = 2V_{OV} + V_T$

$$\therefore V_{min} = 2V_{OV} + V_T - (V_{OV} + V_T)$$

$$= V_{OV}$$

The diagram also shows a schematic of the cascode circuit with a V_T battery connected between the gates of M_3 and M_4 .

We can do for r_o calculation by putting $g_m v_o$ for this r_o parallel $g_m V_{GS2}$ both are in as you said you are in saturation. So, these are equivalent circuit I applied V_x source pass I_x current, why V_{GS2} is 0 I said because the source is coming from reference and that I must actually create it to 0 no current in the reference all sources

current sources be opened and voltage sources should be shorted. So, the other side of circuit is not necessary because they are I am forcing V_{GS2} to go to 0, now if I do this you can see $g_m V_{GS}$ is also will go away.

So, if I calculate this value $g_m V_{GS4}$ multiplied by parallel combination this. So, R_{out} will come which we did earlier is $g_m 4 r_{o2} r_{o4}$ which is essentially gain times the r_o . If r_{o2} and r_{o4} are equal then you can say $g_m r_o^2$ is that correct; what is the output resistance of a CASCODE $g_m r_o^2$. So, we will achieve higher output resistance by simply cascoding at what cost I did this. I had to have 1.57 V min for this current source to operate as a good current source is that clear. So, the conditions which I thought we can achieve by just cascoding was not sufficient is that point clear. I have improved r_o , but I also saw it has improved increase the V_{min} which I as I said my first characteristics.

Ideally I want V_{min} to be close to 0, or very sharp rise very small V_{min} then it is a good current source. I am trying to reach that. So, why are we looking into this to reach there will one by one go step bias. So, I said first we went for simple then we say it is let us CASCODE. So, I brought r_o out higher and now I want to keep this output stay similar because I do not want to reduce my arrow, if possible I may want to increase it further, but I want to now reduce V_{min} . So, what should I do so that I can reduce V_{min} ?

Now, what we do is we can reduce the V_{min} by very funny circuit is done, this is called magic battery solution this solution is named as magic battery solution. The rest part is similar except that please do not worry too much circuit is same as what it was.

Except that between the gates of M_3 and M_4 I have applied a small battery of V_T . And that is why it was called of course; there are number of variations on this I am giving you the simplest on them there are four such circuits which can do similar things one of them we will see. So, what is now happening is we have this $2 V_{OV}$ by V_T which we have got in minus $V_{OV} V_T$ because this additional V_T we are supplying now which will get subtracted. So, now, we are getting V_{OV} as your V_{min} . So, we have reduced from $2 V_{OV}$ plus V_T to only V_{OV} which is what you say smaller. So, I putting a battery to compensate I will be able to reduce my V_{min} , but no cost at output because I CASCODE stage is not change by me is that correct now may be you look into the book.

There are variety of course, this name is not given by baker, but this is an interesting name I read somewhere it is called magic battery solutions. How to create this V_T is what the solutions are, different way you can create V_T s and then you can see that you can compensate for please remember this is opposite sign that is why it is deducting actually this technique of readjusting the V_{min} by adjusting additional batteries you can have multiple there are multiple systems. So, maybe you look in to book this is just give an idea how V_{min} can further be reduced, normally batteries are not put like this. So, some other method will use to put V_{min} V_T there equivalent source equivalent reference. So, I need a voltage reference there. So, now, we must look for voltage reference because I have I need that somewhere here to get it, but as far as theory is concern if I can put some value there I can minimize this value is that this.

Student: (Refer Time: 20:02).

If you change the V_{GS} corresponding the; this voltage plus this voltage this $2V_{OV}$ minus this if you subtract, then the V_{DS} will be this to this will be this try yourself substitute the values. For every node the method I will suggest you every node you calculate voltages and find voltage here and find voltage there V_{DS} of M_2 , but that additional that will be same V_{DS} because that that I cannot minimize because that will decide by my current which I will push, but at least here it was V_{OV} plus V_T that V_{TI} I have actually cancelled where point is sorry I think you are also right, this value which I have reduced here it was V_{OV} plus V_T that I have actually reduced by $1V_T$ by putting a battery is that correct. So, overall $1V_T$ reduction I had done this is just you can see $1V_T$ only I am reducing out of it that V_{GS} I had subtracted $1V_T$. I can readjust this value to some further reductions, but the problems is I reduce this too much this transistor may not remain in saturation.

Student: (Refer Time: 21:11).

So, how much V_T to adjust I have how much battery to adjust is force by me M_2 to remain in saturation. So, this is what I thought that this is good enough and that is the minimum I should start with. So, at least $1V_T$, V_{min} I have gone down is that sorry I should not have said, this is not be this is what we have said is correct this is at V_{DS2} is the value which I got you are really good. The another thing which is worrying me on any current source and current mirrors is something which is you know in real life

no parameter remains constant is that we have seen variability issue. So, how do you monitor variability what is the method of finding variability.

(Refer Slide Time: 22:10)

Sensitivity Analysis

Definition: $S_x^y = \lim_{\Delta x \rightarrow 0} \frac{\Delta y/y}{\Delta x/x}$

(1) Sensitivity of Current Source wrt V_{DD}
 In a Simple Current Mirror (W/L are equal for M_1 & M_2)

We have $I_0 = I_{D\&S1} = 10 \mu A$

However $I_{D\&S1} = \frac{V_{DD} - V_{DS} - V_{GS}}{R}$

We need to find $S_{V_{DD}}^{I_0} = \lim_{\Delta V_{DD} \rightarrow 0} \frac{\Delta I_0/I_0}{\Delta V_{DD}/V_{DD}}$

or $S_{V_{DD}}^{I_0} = \frac{V_{DD}}{I_0} \frac{\partial I_0}{\partial V_{DD}}$

But $\frac{\partial I_0}{\partial V_{DD}} = \frac{\partial I_{D\&S1}}{\partial V_{DD}} = \frac{1}{R}$

$\therefore S_{V_{DD}}^{I_0} = \frac{V_{DD}}{I_0 R} = \frac{2.5}{18 \times 390 \Omega} = 0.4$

$\frac{\Delta I_0}{I_0} = 0.46 \times 0.2$ (if V_{DD} become $V_{DD} \pm 0.1V$)

So, one method is called sensitivity analysis is that clear what is sensitivity here is a definition of sensitivity. I want to find variation of y with reference to variation in x is that I want to find sensitivity of y with reference to variation in x. So, it is defined as limit of x to 0 delta y by y upon delta h by x this is the definition of sensitivity of y.

Student: (Refer Time: 22:33).

If this is my sensitivity for more details please read Boyce and Baker's book if I have missed something you actually look further circuits there. Because now I do not want to spend all the; my time in only current sources I have limited time. So, I only showed you the method what they are trying and that is what we are looking for. So, let us look for this sensitivity of current source with respect to which parameter is the first parameter I should look into the power supply, because power supply is never a constant quantity it is externally connected from the pad and that can vary because of a variety of reasons particularly opamp, we actually look for that variation in what term we call they are power supply rejection ratio if there is a variation of V D D what happens. Here there is no p s r, but we just want to know what is it let us say for a simple mirror I calculate my sensitivity. So, it is I D S 1 is equal to I D S 2 w bias are equal then I 0 is I D S 2 which is equal to I D S 1, but how much is ids one we have calculated V D minus V S S minus

V G S please remember where drop across this, plus drop across this plus V S S is essentially met V D D.

Is that correct R R plus V G S plus V S S is V D D. So, I can evaluate I D S 1 from that V D D minus V S S of course, this is minus of minus, so it will add minus V G S upon R. Now we want to find the sensitivity of I 0 because that is my output with reference to variation in power supply voltage. So, I define it is limit of V D D tends to 0 is a small value delta I 0 by I 0 delta V D D sorry yeah sorry. I made a mistake everywhere please check it you are a very good. So, this if I rewrite this is equal to V D D by I 0 partial derivative of I 0 to V D D. So, it is this is my S I 0 V D D is V D D by I 0 delta I 0 by V D D.

But if I see delta I 0 by V D D from this term which is delta ids one by delta V D D, if I differentiate this equation of I D S 1, I get one upon R is that correct. So, if I get 1 upon r because these are constants. So, I leave them delta I 0 by I 0 if you are look at it I substitute some values, but first let us look at this is V D D 0 by I 0 R and the expect value which I last time used value is this R is 380 k for a 5 4 supply, 5 4 means 2.5 V D D and 2 minus 2.5 V S S is net 5 is that clear 2.5 V D D and minus 2.5 V S S. So, sum total is, but here only V D D I am looking V S S I am still keeping constant. So, 2.5 point 10 to the power minus 5 into 380 I 0 is let us say 10 micro amp current.

Assumption is I 0 in our case example is 10 micro amp current that is what we solved the problem. So, this is what it is. So, this gives me a sensitivity of .66. If I want to know the change in current of I 0 then .66 .2 about 2.5 which means if V D D has change a .1 volt plus minus .1 volt this is the kind of percentage variations you can get in I 0 is that clear. So, this is the sensitivity, but I 0 will change if V D D changes is that correct, this is essentially why we are looking this because we constantly say I want constant current source now this constant what is how many how much constant. So, what should be the idea here whether this sensitivity should be larger or smaller as small as possible because I do not want current to change with change in V D D.

Or very small change in R 0 with reference to large change in V D D that happen I say I have closer to my constancy of current, at least from the power supply side. If that influences directly I change 1 percent either 1 percent 10 percent also then I will worry. So, at least it should not be it is less than 1 any way. So, at least you have (Refer Time:

27:22) by this kind of sourcing you did. So, this is one parameter which is the other parameter we should worry about in variations, one is power supply value what else when the circuit is working somewhere what is it changes because current is flowing.

Student: temperature.

Temperature, so the next value is temperature variation is that sudip, the first is power supply voltage variation the other is temperature variation and temperature variation is many times much stronger. In fact, because device is normally operate from where to where. In many operation as much as minus 25 to 150 or 125 or minus 40 to some 105 degrees, this is new standard, military standards. So, device may even ambience may vary in it is own temperatures or device during working I square R last will keep hitting the device unless you dissipated properly. So, if the temperature variation is a crucial fact for us to figure out whether R 0 will change at different temperature. What do we expect should not change that is what I ideally will like.

(Refer Slide Time: 28:39)

(*) Temperature Sensitivity

$$TC(I_0) = \frac{1}{I_0} \frac{\partial I_0}{\partial T}$$

$$S_T^{I_0} = \left(\frac{\Delta I_0 / I_0}{\Delta T / T} \right) = \frac{T}{I_0} \frac{\partial I_0}{\partial T} = T \cdot TC(I_0)$$

$TC(I_0) \Rightarrow$ evaluation

$$I_0 = I_{DS1} = \frac{V_{DD} - V_{GS} - V_{th}}{R} \quad \text{for Simple Mirror}$$

$$\frac{\partial I_0}{\partial T} = \frac{\partial I_{DS1}}{\partial T} = -\frac{1}{R} \frac{\partial V_{GS}}{\partial T} + \frac{1}{R} V_{GS} \frac{\partial R}{\partial T}$$

$$\therefore TC(I_0) = \frac{1}{I_0} \left[-\frac{1}{R} \frac{\partial V_T}{\partial T} - \frac{1}{R} \frac{2 \sqrt{I_0 R}}{R} + \frac{1}{R} \frac{\partial R}{\partial T} \right]$$

Typical value $TC(I_0) = 0.17 \% / ^\circ C = 1700 \text{ ppm}/^\circ C$

The temperature variation sensitivity is expressed as temperature coefficient is different defined as temperature coefficient ok, sometimes they write like this some may be I will write like this ok.

Student: (Refer Time: 28:49)

T_C is capital f is subscript. So, $T_C f$ temperature coefficient of I_0 is defined as one upon I_0 , $\frac{\Delta I_0}{I_0} \text{ by } \Delta T$ this is how temperature coefficient of I_0 will be defined. We already have written sensitivity of I_0 to temperature if we can find out. So, it will be I same this take again limit of ΔT tends to 0, $\frac{\Delta I_0}{I_0} \text{ by } \Delta T \text{ by } T$ I T by I_0 $\frac{\Delta I_0}{I_0} \text{ by } T$. So, you can see from here there is a relationship between sensitivity and $T_C f$ is that clear this part one upon I_0 $\frac{\Delta I_0}{I_0} \text{ by } d t$ is nothing, but $T_C f$ of I_0 you look at it $T_C f$ of I_0 is one upon I_0 $\frac{d I_0}{I_0} \text{ by } d t$, in differential this I get one upon I_0 $\frac{d I_0}{I_0} \text{ by } 0$ multiply to T . So, T times the temperature coefficient if I put f of I_0 is sensitivity.

So, if we have been given sensitivity and temperature of operation and actually specifying temperature coefficients is that clear all vice versa. So, again same thing data is given in some cases in S form some cases in T shape form, but both are anyway interrelated, let us calculate $T_C f$ what is I_0 I just we wrote it will be is it. So, far so good I_0 is $I_D - I_S$ which is $\frac{V_D - V_S}{R}$ for the simple mirror I differentiate. So, it is $\frac{d I_D - d I_S}{I_0} \text{ by } d T$ and I differentiate this term with reference to temperature now which are the terms which are functions of temperature, we assume V_D and V_S do not change with temperature ok this is also not very valid statement every time.

But assume it right now, but mostly yeah we can assume that, but which is the strongest function of this temperature the resistance which are the direct change in resistance occurs with the temperature, but V_G also changes because V_G has something to with V_T which we have $V_O + V_T$ so obviously, I must look for V_G variation with temperature and I must look for resistance variation with temperature. So, I differentiate this two terms. So, one upon R $\frac{d V_G}{d T} + \frac{1}{R} \frac{d V_G}{d R}$ if I do this then I get R to be $\frac{1}{R} \frac{d V_G}{d T} + \frac{1}{R} \frac{d V_G}{d R}$ [FL] you are right differentiate [FL]. So, I have done substitute this $\frac{1}{I_0} T_C I_0$ and if I whatever just they verify properly $\frac{1}{I_0} \frac{d I_0}{d T} - T_C$.

So, now I substitute V_G is that correct what is V_G , V_G is equal to V_T under a 2β I oh sorry I by β , if I do that then I can actually look for this expression. Similarly this just check you know may be I have I say in adding I might have done some issue, but just check it well. So, basically what is T_C or $T_C f$ if we keep calling same name everywhere, if you substitute for both values are simple mirror 380 k and 1.2 volt V_G V_T upon .38 volts, we can substitute those value and we figure it out this is .17 percent

per degree centigrade typical, but normally all T C S are expressed in what numbers not in number they always expressed in part per million 1 into 10 to power 6, that is the unit they normally use.

So, if it if you convert this into part per million, It is 1700 part per million per degree centigrade is the temperature coefficient of I_0 by the way 1700 is not a large value compared to other value which may be 3000 or sometime 2400. So, this value is not largest among the values which are used in my analysis resistance. In fact, you calculate this is typically around 3000 for the actually resistance I make in chip. So, it is largest variation come from resistance further this comes from V T variations. So, we will see how much variation temperature depend each has how much ppm they have, but this is to give an idea typically the source currents are 1000 to 1500 to 2000 ppm per degree centigrade rise is always seen with the temperature.

So, now you think of it if I increases it by some amount of temperature the current will correspondingly change proportionately and are you really accepting that much change if that is acceptable to you for your device circuit further is no problems, if you do not want that then think of it to adjust these values what should I do you can see if I can sum how these two terms equal plus and minus I can bring down that value; that means, I design it something, but we design this if I change my W value or V G S are anything or V T then what will I change whether that M 2 M 4 will remain in saturation I am not guaranteed. So, I must first go look to verify every time there because my R 0 guarantee I am I must ensure that R 0 is higher. So, by doing this I must see that my other factors are not terribly disturbed and that is where the design starts at how much T C f you can have to adjust what best R o we can get.

At what V minimum you can get designed whichever is possible that is the source for you is that correct, but in simple mirror R o is not very high. So, we any way going to do CASCODE of that with battery magic battery there. So, that further reductions in V min I can attain and also I have higher R o, but with that I am not done this with that I must calculate now T C f I_0 and figure out whether it is lower or higher than 1700 for those simple mirror, if that is much higher how much tolerance you have, verify yourself with that happens fine otherwise go back any design everything is that issue clear to you, parameters I am worried about it is saturation of M 2 M 4 to get my R 0 higher, I learn V minimum.

So, I will use some other circuit part is V minimum and then all that with that W bias I will use I figure out my T C f is too high and I want to re change everything, that is where the design starts given this value how much tolerance I have because designers do anything at the end of chip it should follow you. So, what it will give you will have to model it back and say oh I have did not take care of T C f therefore, this values are gone out. So, this such a situation you must take in designs ok.

(Refer Slide Time: 36:36)

1. $TC_f(R) = \frac{1}{R} \frac{dR}{dT} \approx +2000 \text{ ppm}/^\circ\text{C}$
 where R is created from Diffused n+ region

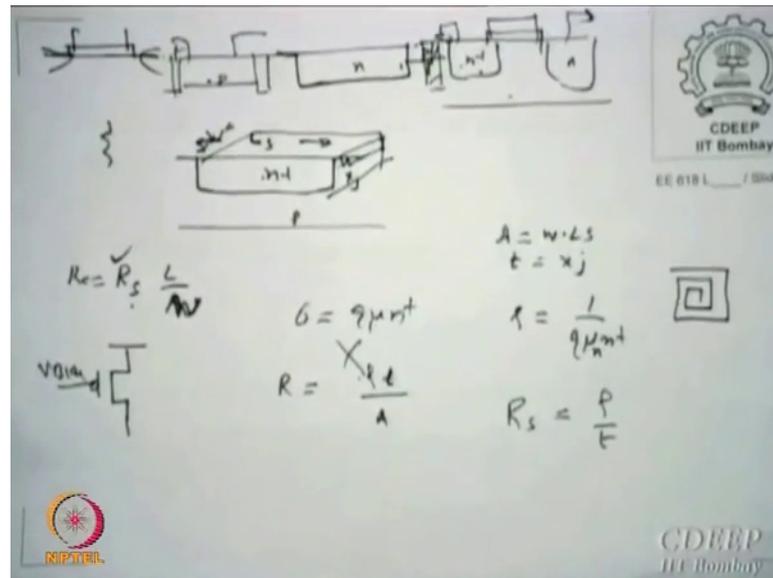
2. $TC_f(V_T) = -3000 \text{ ppm}/^\circ\text{C}$ for $V_T \approx 0.8\text{V}$
 Typically $\frac{\partial V_T}{\partial T} = -2.4 \text{ mV}/^\circ\text{C}$

3. For a MOSFET $\beta' = \mu C_{ox}$, $\therefore \beta'(T) = \beta'(0) \left(\frac{T}{T_0}\right)^{-3/2}$
 This gives $\frac{1}{\beta'} \frac{\partial \beta'}{\partial T} = -\frac{1.5}{T}$, T in $^\circ\text{K}$
 or $TC_f(\beta') = -\frac{1.5}{T} \times 10^6 = \frac{1.5}{300} = \frac{1}{200} = \frac{10^6}{200} \text{ ppm}/^\circ\text{C}$
 $= 5000 \text{ ppm}/^\circ\text{C}$

The slide also features logos for CDEEP IIT Bombay and NPTEL.

Search for the (Refer Time: 36:30) of it I will just give some values for you to values to see what they gives typically a resistance which is used in diffusion n plus region of source in whatever you used in a mass transistor, if I make a resistor out of n plus region how do I make a resistance of n plus region anyone may be I will show you quickly.

(Refer Slide Time: 36:51)



This is my n plus area, this is my junction depth in p, ok this is the source drain lengths what we call L_s or L_d whatever it is and if you see it another dimension which is w this is my w . So, the area is w into L_s thickness is x_j and the resistivity of this sigma is $q\mu_n n^+$. So, I know ρ which is one upon $q\mu_n n^+$, μ_n is known n^+ is known, R is ρ that is ρl by A by A t of course, ρt by A So, I can calculate the length of this source region though you source has source in the transistor as used another say for example, the resistors are make something like this is your transistor for example, plus another n^+ region is created here ok.

And the resistor is built in that that is how ICs are made, whichever component you want you should put another region for that what is the problem with such putting there what is the criteria I should have, this is n^+ this is n^+ this is n^+ , but this is p isolate now how to isolate the two areas, this either put an oxide down here which is a s t r or this n p n transistor should have a gain of less than 1, is that clear or put even higher doping here. So, that the gain goes down it is called guard ring. So, put either a guard ring or put isolating diode oxides below trench it down and separate the two areas ok, that is the basic requirement to make any other component. So, every component in this circuit has to be isolated from the others by either of these techniques and that cost hell of money.

Student: sir.

Yes.

Student: (Refer Time: 39:07) for the resistance.

This is a resistance known [FL] bar of semiconductor has length, width and thickness. So, $R = \rho \frac{l}{A}$ so I have just only lengths and width is given by w which is given to us. So, I have a longer l and l in region or this decides my resistance typically even this is not done because n plus is not a constant quantity. So, it is actually given by R is equal to $R_s \frac{l}{W}$ by a sorry l by W , R_s is called the sheet resistance of the n plus region which is typically may be 10 ohm square or 15 ohm square or sometimes even 1 ohm per square in some areas.

So, R_s is known to me from technology, W is generally used as the standard widths and the lengths are only adjusted to get your sheet resistance or proportional that are you I need want is that this is how all resistances are made, which is the higher resistance if I want to what should I use which area I should use, n plus in a very low resistance because n plus is a higher doped regions. So, conductivity is higher. So, what should I which area I should use P region. So, I actually I have another this reference and this P region I have another P created in the P which is the dope sheet resistance of my choice and then make a contact here to make a higher resistances is that clear. I have P region created in the P value itself and make two contacts separated length L to be my sheet resistance into L by W values.

Why I said P will have a higher resistivity and therefore, higher sheet resistance how can we I increase or decrease sheet resistance other than the this what is sheet resistance I have defined anyone ρ by T thickness I can adjust even thickness, but normally I cannot separately implant something here and separately implant if I already doing implant I will open a window and implant write there, but the higher resistance are I will have to implant anyway. So, for a more resistance the source area that is area whatever n plus I am doping same I use it for low resistance values, I will only adjust this lengths for them and width of course, standards. So, I will get mention resistance of that, but if I want to higher I can even do better I can deposit anyway I am going to have a poly here. So, I can have a poly layer of course, it has to be also protected by oxide and I can make a contact to poly.

Because poly has a very high resistance relative to everyone else ok is that clear another mass please remember what is the orient technology everything I do individually I required every other area to be must do process there [FL] [FL]. So, now do we really wish to do that because how many means many is money how money I have [FL]. So, everything is not. How do I capacitors in this technology I have a M O S [FL] mass capacitors sitting there, but there are other capacity methods also and I also have a transistor and ground it both side, this is the good capacitor if connect gate to the source I will make a diode out of it I showed you earlier diode connections.

So, I do not make any additional device in the I C I only convert my M O S technology areas into variety of component, what I cannot do then resistor I did capacitor I did diode I did inductance is nothing I can do for about, all that I can do a print a spiral on the top of this and that is very difficult gain you know and it should you some it takes. So, much area make a small inductance mainly .1 nano and there is a still require some 20 tons or 18 tons and that area if you see a R S circuit ninety percent of R S circuit area is because of the inductances. In analog chip except for V C O where they will actually go to inductance will never use inductance anywhere even in filters which we will do possibly I replaced L by something ok.

Student: (Refer Time: 44:02).

By using switch capacitor I use I c a as combination and every l I will replace at by c. So, I will never use the inductances as far as possible in analog I will only use capacitors, I will use resistors also out of the same and I will use mass transistor and nothing more than nothing less that is how the integration is possible. So, please do not think that I any even if I show you this essentially what I am going to do is the following, a P device properly biased it acts like a resistor. So, I am not actually going to use any time a resistance anywhere is that clear to you. So, please take it that in real life on a chip only mass transistors are preferred everywhere convert as much as you can it is [FL], but that is all that I will give you ok.

So, this has to be understood that in I c technology the reason is size w by l I want to see smaller any other way I go it will be larger. So, I will it will not be as good. So, what is the problem, the sheet resistance I am sort the T C f of this and T C f of this is different in sign and that is the problem starts, then should we not really put a resistor to

compensate. So, that is what band gap reference people do they actually put a resistance to compensate, they do not put mass device or any other device to compensate they actually use a resistor because it has a opposite sign of T C f oh you want to subtract. So, please remember different components have different way of looking of it in a given circuit this is some additional examples I gave you.

So, for the given n plus region coming back to our analogs $T C f R$ is $1 \text{ upon } d R \text{ by } d T$ which typically for n plus region in 2000 part per million per million degree centigrade, T C f for threshold I think this value you must be aware of those who have done second year course it is del change in threshold voltage with temperature is typically 2.4 millivolt per degree of centigrade with a minus sign that is decrees into that point. So, for the typical point at 3 value of this T C f becomes roughly minus 3000 ppm per degree centigrade typical as I have said please remember in T C f $1 \text{ upon } V T$ is the value coming for. So, this value will be function of V T itself which V T you are using is that ok, what is T C f of V T, $1 \text{ upon } V T \text{ delta } V T \text{ by } \text{delta } T$. So, $1 \text{ upon } V T$ has the value which you have to at different V T this will be large.

So, smaller V T what will happen T C f will be even larger is that clear minus larger then this is around .8 volt V T s this 3000 to 3500 is typically a ppm per degree centigrade is T C f, for a mass fact how much is this in the dipolar (Refer Time: 47:19) the delta V B by delta T, there we calculate how much base emitter voltage changes with temperature.

Student: 23 millivolt.

23 millivolt to 2.3 millivolt per degree centigrade similar numbers not exactly same number [FL] That is the way similar thing that there for a mass fact beta dash is $\mu c \text{ ox}$. So, if I see mobility variation in this it can be written as beta dash $0 T \text{ by } T 0$ to the power minus 3 by 2 this is temperature dependence of mobility, this gives one upon beta dash delta base roughly equal to minus 1.5 by T where T here is in Kelvins.

So, typically T C f for beta dash for the values which I have used could be around 5000 part per million very large T C f for these device beta dash. So, I have seen as yesterday we are saying na beta dash is the very strong temperature dependence, please remember this is for the Boyce Baker's books zeta based on that calculations I have been done for different values we will have to figure out actual values there. So, do not say sir [FL] expression remains same data you substitute of course, 5000 will not become 25000 [FL]

it may become 5500 4500, but it may not be a 5000 for all cases to we handle now we have seen sensitivity due to power supply and sensitivity due to this.

So, now when I am when I am designing a current source all these areas are in my mind, how much current I want how minimum voltage I want how much R_o I want and how much is the sensitivity of say both for V_{DD} and V_T temperature I have based on that only my design will be a good current source is that clear ok. We will have another current source which slightly improve some of them not necessary all of them we know the variation occurs how do you get rid of variations in a normal circuits, world is not I mean you are right work compensation, but what do we really do feedback negative feedback stabilizer everything. So, one technique of improving this is to actually use negative feedback [FL].

That is what the negative feedback do. So, based on negative feedback and a simple current mirror value we can improve some of the sensitivity issues and to such most popular current mirror which are available one is called Wilson mirror other is called regulated CASCODE both uses negative feedback in their sockets.

(Refer Slide Time: 50:35)

Using -ve feedback, Simple Current Mirror can further be improved. Two such circuits are

1. Wilson Mirror
2. Regulated Cascode

Wilson Current Mirror:

By Using P-device with proper bias we can create stable & Reference Current I_{ref} . V_{Bias} is normally taken from a 'Stable Band Gap reference'

This Current Mirror has

- (i) Is much stable than Simple
- (ii) Output Impedance is further improved.

The diagram shows a Wilson Current Mirror circuit. It consists of three MOSFETs: M_1 (PMOS), M_2 (NMOS), and M_3 (NMOS). The gates of M_2 and M_3 are connected together and to the drain of M_1 . The source of M_1 is connected to V_{Bias} . The source of M_2 is connected to ground. The source of M_3 is connected to the drain of M_2 . The drain of M_3 is connected to V_{DD} . The output current I_o is taken from the drain of M_3 . The reference current I_{ref} is taken from the drain of M_1 . The gate of M_1 is connected to V_{DD} .

Just now I said it and now here that circuit this R has been replaced by a P channel device, now the question which we should ask what is this V_{bias} this value we know that M_1 must remain in saturation so that resistance is constant. So, how do we fix V

bias? So, we need where voltage reference which is be constant actually use connect their; I repeat what I say I need a constant voltage source which I can connect here.

So, I will also be after the current source I will also try to see; what is voltage references available and how to constancy I see their sensitivity temperature in specific and value with the power supply variations. So, if device constant I can connect them here, that value will push a fixed amount of resistance have for this and flow a current of my choice through a M 1 and therefore, M 2 is that. So, V bias as of now I say it is constant how do I get that constant is also a gain. So, we will see of course, there are another way of doing it instead of actually doing it you can use a feedback also to keep V bias constant. So, it will give some tricks there also [FL] and then it does not work itself.

So, we will see that now [FL] here is Wilson mirror one mirror what resistance did where the CASCODE area. He did not change anything on the simple reference side, however he has a CASCODE on the output side because r o you do not want to reduce I kept this series like this, but what I did is the output of the first this stage or into drain I connected to the gate of M 4 now let us see how it feedbacks please first you do not write think only first here just draw this circuit and let us discuss first. So, start looking I right now assume because of my fixed bias this current which need not be call I D S 1 may be call I reference whichever book something said is constant is that clear, I D S 1 is that constant current generated because V bias is fixed by me, I know variations are I have taken care of all of it as a this current is constant is that clear. Now let us say first for some reason R 0 increases if you say this current increases what will happen.

Student: (Refer Time: 53:35).

That means this voltage drop will increase, which means this current will increase. If this current increases what will increase, this current will increase because say mirror part of that, if this current increase then this is constant this voltage must go down ok because you are pushing it top and now you are asking it to increase.

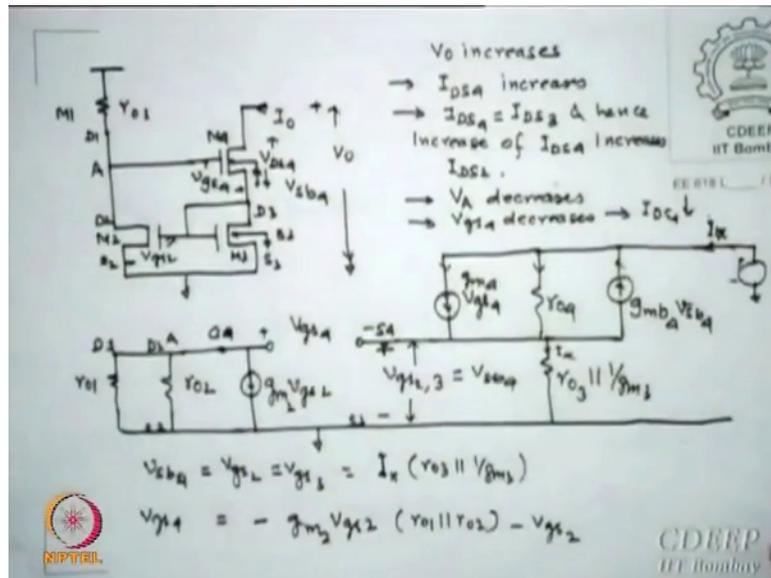
So, this voltage must goes down if this voltage goes down V G S 4 goes down. So, R 0 reduces if it goes too low the opposite will occur this will push till both side match. So, this is what essentially negative feedback does is that clear and since negative feedback allows you to stabilize, which is the standards of stabilizing anything you can use a partially CASCODE mirror using Wilson current mirrors, Wilson connections and say

that it will see much better than normal CASCODE sources is that clear to you did not get it $I_{D S 1}$ is constant, but by force you are trying to change your $I_{D S 2}$ is current from mirror from M 3 side [FL] what was saying is how can it happen no it will not if that is what feedback gives how feedback will push that same current is what I am telling is that point clear to you your idea is in a circuit two currents cannot go that is exactly I am also saying is that clear to you because two currents cannot flow, but now I am forcing this to increase which means this voltage must go down because I add drop will go down.

So, then this $V_{G S}$ falls. So, this current will reduce them is that correct because we say $I_{D S 1}$ has to be $I_{D S 2}$ is that clear. So, how the feedback will force that issue that is one only current will flow down, if one there is a variation in I_0 is what I said and therefore, I_0 will become constant independent of anything; this is called Wilson's feedback system. These are simple statements nothing very wait current there has I_0 must stable than the simple mirrors output impedance is further improved because of the CASCODE connections ok.

I already said for those I made a statement the V bias is normally taken from the stable band gap reference which will look into can you think why there also it is a constant must be there also should be feedback because other way it cannot create a constant value. So, a band gap reference must have some comparisons it must find errors and feed it back. So, that it reaches to a constant value. So, we will see that later is that everyone this is $V_{G S 2}$ this is $V_{G S 3}$ ok.

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Now, we see this is V_{GS4} this is V_{DS4} this is what we said as far as the P channel device is concerned it is now only acting like a current source with a resistance of r_{o1} and that is a constant current source because we say V_{bias} is fixed. So, we do in IC we do not consider that that is a fixed source, but this r_{o1} will appear for that because there is a output resistance of that P channel device ok.

So, as far as I am concerned for the first transistor only r_{o1} from gain to source is available. So, I have plotted it here for the D2 for this V_{GS2} by the way what I am calculating I am calculating I am doing a V_x here and finding V_x by I_x to get R_{out} I am not doing anything, I already shown you here I am trying to find R_{out} from substituting putting a V_x source and finding R_x there, on the transistor D2 it is r_{o2} shunted by $g_{m2} V_{GS2}$, but this D2 is create of M4 is that clear, please check it D2 or D1 is g_{m4} [FL]. So, this D1 D2 g_{m4} are same connections.

D1 D2 g_{m4} are same connections is that this terminal this terminal and this terminal are same. So, this is that line three of them D1 D2 g_{m4} now you see what is the V_{gs} is coming here which is same as A voltage minus the source voltage of M4 is the V_{GS4} is that correct. So, the S of this transistor M4 and the voltage here subtraction is V_{GS4} . So, this is my gate this is my source the gap voltage drop between gate and source for 4 is V_{GS4} sign please check it this has to be plus because this is an n channel device. So, this is plus and this is minus for S4 is that ok.

So, this V_{GS4} why I have drawn this circuit is this you should also see that the way I see a circuit I can make an equivalent right there and then I will say they shunt have an [FL], but basic idea is just to substitute whatever you are looking for making an equivalent, my suggestion to you is this method is always correct. Because we are only following node and from there whatever you are seeing you are substituting there the S_2 and S_3 are same which I ground it S_2 S_3 source of M_2 M_3 are connected and grounded S_2 S_3 are connected and grounded.

Now I have to see drain of 4 this. So, this is my where I am actually going to push the V_x I_x currents V_x force and I_x this, which is my I_0 which I am looking for say this term step what is the current source g_{m4} V_{GS4} shunted by R_{o4} just wait for this if I say and just now someone was asking if the source is crack bulk is grounded between source and this there is a voltage now V_{sb} is that correct; however, the V_{SB} I can see V_{SB4} is nothing, but the signs I am putting plus minus for the source which is essentially equal to V_{GS2} and V_{GS3} , V_{GS1} where V_{GS2} V_{GS3} because they are connected with this is same as this potential.

So, I say V_{SB4} is nothing but V_{GS2} or V_{GS3} is that correct. So, this voltage so this is my S_3 this is my S_4 this is V_{GS2} which is equal to V_{SB4} and since please remember this is V_{SB} opposite polarity current pushes up g_{mb4} V_{SB4} . Now this is the equivalent for this for n_3 is g_n term will appear there because this is a diode connection. So, in the R_{o3} parallel g_{n3} I kept it R_{o3} you can even neglect R_{o3} because g_{n3} will always larger than 1 upon R_{o3} therefore, that, but right now I kept I always say I related because I do not know what currency we are going to use. So, I want to retain them in case they are compatible make it parallel.

Now this is very big circuit looking, but there is nothing big part in that. So, first thing I calculate is V_{SB4} , V_{SB4} is V_{GS2} same put same node V_{GS3} now look at the current which is passing through this drop is V_{SB4} is that correct, drop across R_{o3} and g_{m3} and what is the current flowing sum total of these three what are current in this is essentially net current. So, current coming out is also I_x [FL] no current. So, all this I_x current flow through R_{o3} parallel $1/g_{n3}$ is that current that is your V_{SB4} .

So, I get V_{SB4} is V_{GS2} equal to V_{GS3} is I_x times R_{o3} parallel this, now I want to calculate V_{GS4} how much is V_{GS4} we find where this voltage and if I find this

voltage is that point clear how does I calculate V_{GS4} this voltage minus this voltage is that correct that is my V_{GS4} . So, I write how much is this voltage $g_{m2} V_{GS2}$ parallel combination of R_{o1} and R_{o2} is that correct. So, this is my voltage here is that should be clear the voltage drop across parallel combination of R_{o1} , R_{o2} is nothing but the voltage across this that is V_{GS4} how much is V_{GS4} the V_{GS2} just now we wrote that please remember this voltage is this voltage so you subtract this is that clear.

So, we get V_{GS4} is minus g_{m2} we get this minus V_{GS2} is your V_{SB4} , but what is V_{GS4} now why I am interested in V_{GS4} because I want to find drop across because of this. So, I want this current source is that ok, everyone please write down this circuit is as I said you can simplify circuit by parts and can directly write many things please do not write, because this gives you a actually features what is happening there is that correct not only for this circuit for any circuit if you have more than one transistor on the top please put three layers of them actually match the nodes correctly that will never make any mistake in evaluations at the end. So, this is I am not saying this is the method, but this is much simpler method of doing things.

And I am saying this from my experience, but you can do much better you can simplify circuits much equivalent of what is the other method, for each stage find equivalent familiar source and in terminal resistor you place there they are keep doing that also is a equally good method, but doing that essentially you are partly doing the same thing which I am doing I am doing all together that is it Is that correct. So, my method is no different from the other methods given in the books it is same I am only trying to see visualize what this circuit is doing. So, I actually show you what is the equivalent of that from there please do not think it this is diode technique or something before we quite let us finish this today.

V_{SB4} is the between the source because please remember there is a drop here which is the source voltage for $D4$, $M4$ since subtract is grounded there is a V_{SB4} is that correct, but I know this V_{SB4} is same as because this is the same terminal source here must be same as this and this V_{SB4} this is plus and this is ground is that sign correct, source is that higher potential than the ground. So, that is the way that is why say the way I had drawn I am only keeping signs accordingly what will have and that is why actually I change this sign also upwards ok is that now clear to all ok.

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$$\text{or } V_{gs4} = -[1 + g_{m2}(r_{o1} || r_{o2})] V_{gs2}$$

$$= -[1 + g_{m2}(r_{o1} || r_{o2})] V_{sd4}$$

$$\therefore V_{gs4} = -[1 + g_{m2}(r_{o1} || r_{o2})] I_x (r_{o3} || \frac{1}{g_{m3}}) \quad \text{--- (1)}$$

Further

$$I_x = g_{m4} V_{gs4} - g_{m4} V_{sd4} + \frac{V_x - V_{gs2}}{r_{o4}} \quad \text{--- (2)}$$

From (1) & (2)

$$R_{out} = \frac{V_x}{I_x} = r_{o4} [1 + g_{m4}(r_{o3} || \frac{1}{g_{m3}})] (1 + g_{m2}(r_{o1} || r_{o2})) + g_{m4} [(r_{o3} || \frac{1}{g_{m3}}) + \frac{1}{r_{o4}} (r_{o3} || \frac{1}{g_{m3}})]$$

So, V_{GS4} is that there for equal to minus I will take sign 1 plus g_m to R_1 parallel into V_{GS} just combine nothing very serious, but V_{GS2} is V_{SB4} I just wrote. So, I replace V_{GS2} by V_{SB4} , but V_{SB4} I already calculated I_x parallel multiplied by R_{o3} parallel 1 upon g_{m3} . So, I substitute that here. So, I get V_{GS4} is equal to minus 1 plus $g_{m2} R_{o1} R_{o2}$ into $I_x R_{o3}$ parallel 1 upon g_{m3} is that. So, one equation I figured out in which V_{GS4} is related to this if you look at this circuit once again please write write down this we will come back to circuit again. Only up to equation one you check and then I will draw this circuit is that everyone wrote down this equation see this circuit, this I_x is divided into three currents is that correct $g_m V_{GS4}$ minus $g_m d V_{SB4}$ plus V_x divided by V_x minus V_{GS2} or V_{SB4} by R_4 .

This voltage minus this voltage divided by R_4 this current source and opposite current source, this is the net current which is I_x is that three parts each is this I_x is sum total of these three because you can see below I_x is coming. So, all three must be summed up proper signs. So, in some book sum $g_{m4} V_{GS4}$ minus $g_{nd} V_{SG4}$ plus V_x minus V_{GS2} is that correct V_{GS2} divided by a R_{o4} is the second equation, then I use this two equation and evaluate it V_x by wherever the V_{GS4} is there I substitute it all of it here. Collected the terms for I_x collected terms for V_x and then divide V_x by I_x . So, just check this is R_{o} . So, this is.

Student: (Refer Time: 69:12).

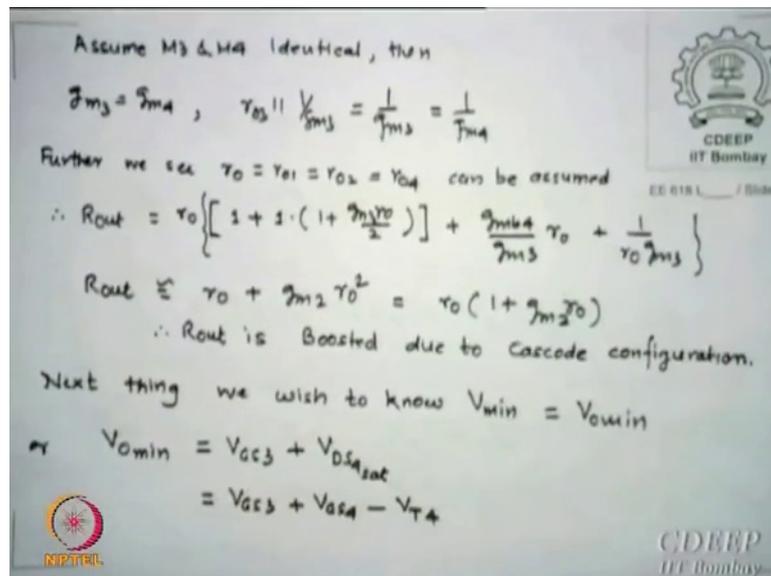
R o I do not know which one, but just check some R o must appear there.

Student: [FL].

[FL] [FL] So, check it all that I say what I did in the paper I actually substituted $V \times V$ G S 4 here $V \times B$ 4 in terms of $I \times$ again and then I collected $V \times$ and $I \times$ terms and divided this is what I did. So, this is what I got [FL] please check it sorry for my mistake I should do that anyway I am really tomorrow I will actually show you correct expression which I got.

In normal cases g_{m3} will be same as g_{m4} because I keep M_3 M_4 identical thresholds are same R_{o3} parallel 1 upon g_{m3} I will replace it by 1 upon g_{m3} , because I know R_{o3} are larger and g_{m3} is equal to g_{m4} . So, I will say R_{o3} parallel 1 upon g_{m3} is 1 upon g_{m3} or 1 upon g_{m4} and call them g_{m} itself pensive I can use that I will also say a one is equal to R_{o2} equal to R_{o} all this mirrors are same. So, all R_{o} s are A.

(Refer Slide Time: 70:34)



If I do all this at the end of the day and let us say g_{m2} and g_{m4} are only one these are this can be adjusted we say roughly R_{out} will come R_{o} plus $g_{m2} R_{o}^2$ or roughly $g_{m2} R_{o}^2$ do CASCODE. So, nothing grate all that I did after all this huge calculations I arrived at saying. That it is $g_{m} r_o^2$ no grate this, but just to say at the circuit is larger things do not change very large all that you have to keep evaluating expression wise longer expression. So, do not get fear of that so obviously, we knew it is

the CASCODE and therefore, it has to boost R_o now V_o minimum is the next thing we will we must want to know man you just write this final expression which is of relevance to you can do whatever you did R_{out} is R_o plus $g_m R_o$ square by cascode the output impedance has boosted gain times R_o $g_m R_o$ is the gain. So, times r_o there is the boosting of that further boosting; how can we do you can use CASCODE with the gain. So, you can further boost R_o in case you need further R_{out} higher.

Some other penalty of power and area you may give what is V_o minimum V_{D4} at the end what I wrote is otherwise I also prove I did not bother to see of I say it should be R_o plus $g_m R_o$ square equivalently, if you see this figure this voltage is this voltage plus V_{GS} . I repeat this is V_{GS} you have come here plus V_{D5} is that correct I repeat again this voltage is same as you reach here this plus V_{D5} of this is by V_{D4} is that. So, V_{GS3} plus V_{D54} is the output voltage V_o . So, V_o is V_{D3} plus V_{D54} sat the transistor must remain in saturation.

So, we say it is what is age of saturation minimum [FL] V_{GS} minus V_T . So, you substitute V_{GS4} minus V_T4 , I can rewrite now V_{GS} how do I write V_{GS} in what terms V_T plus under root 2 by beta plus have you written down this.

(Refer Slide Time: 73:24)

$$V_{owin} = \sqrt{\frac{2I_0}{\beta_3}} + V_{T3} + \sqrt{\frac{2I_0}{\beta_4}}$$
 If $\beta_3 = \beta_4$, then

$$V_{owin} = 2\sqrt{\frac{2I_0}{\beta}} + V_T$$

$$\propto V_{owin} \propto \sqrt{2I_0}$$

The graph shows two curves starting from the origin and leveling off, representing the relationship between V_{owin} and I_0 .

So, we write $V_{minimum}$ is under root $2 I_0$ by beta 3 plus V_T3 plus $2 I_0$ by V_T [FL] a beta here also equal which you can then [FL] 2 into $2 I_0$ beta V_T w by 1 plus V_T . So, now, V_o $V_{minimum}$ is proportional to $2 I_0$ under root of $2 I_0$. So, larger the current

source you are getting by definition or by theory your V_o min will increase is that clear this is now you cannot do much, essentially I am saying V_1 is looks V_o minimum whatever you are getting if this is your this if you want higher currents you will have to sorry yeah you will have to do only this, there is no other way of pushing higher currents if you push higher currents drops will also increase essentially what I am saying [FL] there is nothing I can do only thing is it is not linear like ohms law it is under root of I_0 which is it proportional to it because of the square law term I am getting. So, I can evaluate V_o min how to minimize this I cannot change the I_0 because that is what I am looking for all that I exist is w by L s, but if I adjust w by l what will happen the more current then reference current may not be same.

So, I will have to figure out what reference I should keep. So, that with this w by l I get the I_0 of my choice that you can always think is that clear because the ratio may not be same than then it will transfer in a ratio. So, initial current must be boosted to come to this value if w by l change on the other side figure it out what should be reference current that is how you will be able to define specifically this we will come next time what is we called V_T reference current source.